

GBU6A - GBU6M

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted) (Note 1)

			Value							
Symbol	Parameter		6A	6B	6D	6G	6J	6K	6M	Units
V_{RRM}	Maximum Repetitive Reverse Voltage		50	100	200	400	600	800	1000	V
V _{RMS}	Maximum RMS Bridge Input Voltaç	ge	35 70 140 280 420 560 700		700	V				
V_{R}	DC Reverse Voltage (Rated V _R)		50	50 100 200 400 600 800 1000		1000	V			
I _{F(AV)}	Average Rectified Forward Current	T _A = 100°C		6.0					Α	
I _{FSM}	Non-Repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave		175						А	
T _{STG}	Storage Temperature Range			-55 to +150				°C		
T_J	Operating Junction Temperature		–55 to +150						°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

THERMAL CHARECTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
P _D	Power Dissipation	12	W
$R_{ heta JA}$			-

TYPICAL PERFORMANCE CHARACTERISTICS

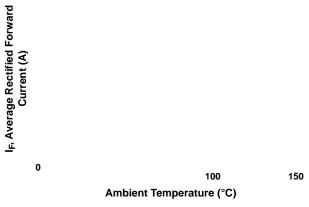


Figure 1. Forward Current Derating Curve

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22.30 21.80

> 2.16 1.6

